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SLVU2.8-4

2.8V TVS Array For ESD and Latch-Up Protection

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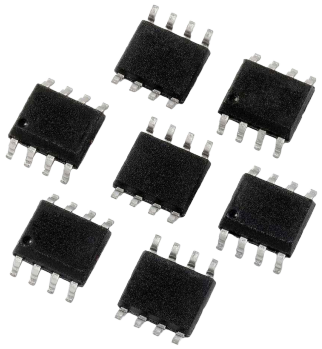
Description

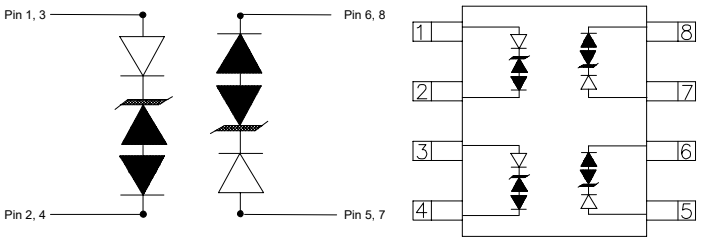
The SLVU2.8-4 is designed to protect low voltage, CMOS semiconductors from transients caused by electrostatic discharge (ESD), cable discharge events (CDE), lightning and other induced voltage surges. Low capacitance compensation diode is integrated into the TVS to lower the typical capacitance to 1pf per line. The SLVU2.8-4 complies with the IEC 61000-4-2 (ESD) standard with ±15kV air and ±8kV contact discharge. The SLVU2.8-4 is assembled into a 8-pin lead-free SO-8 package, The combination of low leakage, signal integrity and flow through design makes the SLVU2.8-4 an ideal application such as 10/100/1000 Ethernet.



SOP-8

Features

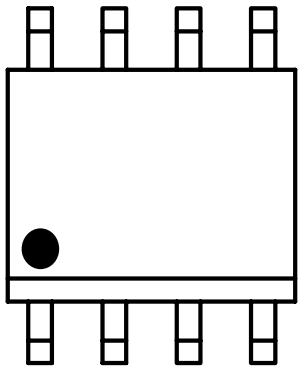
- 400W peak pulse power (8/20μs)
- Protects two line pairs (four lines)
- Ultra low leakage: nA level
- Low operating voltage: 2.8V
- Very low capacitance: 1.0pF
- Ultra low clamping voltage
- JEDEC SO-8 package
- Complies with following standards:
  - – IEC 61000-4-2 (ESD) immunity test
    - Air discharge: ±15kV
    - Contact discharge: ±8kV
  - – IEC61000-4-5 (Lightning) 24A (8/20μs)
- RoHS Compliant



Circuit diagram

Mechanical Characteristics

- Package: SO-8
- Lead Finish: Matte Tin
- Terminal Connections: See Diagram Below
- Marking Information: See Below



Dot denotes Pin1

Applications

- Base Station
- Analog Inputs
- Switch Systems
- 10/100/1000 Ethernet
- WAN/LAN Equipment
- Desktops, Servers, and Notebooks
- Low Voltage Interfaces

Ordering Information

Part Number	Packaging	Reel Size
SLVU2.8-4	2500/Tape & Reel	13 inch

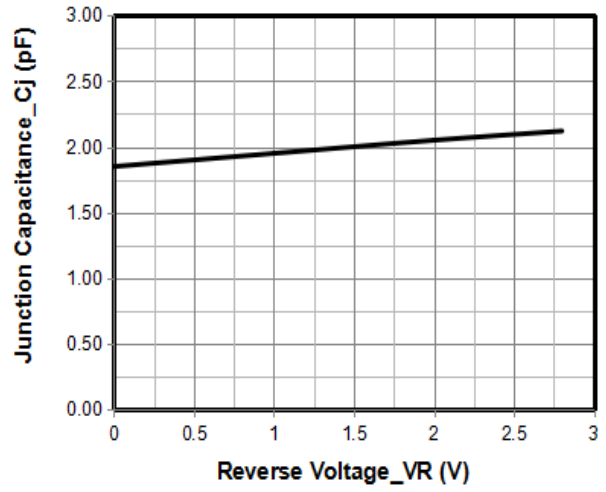
Absolute Maximum Ratings (T_A=25°C unless otherwise specified)

Parameter	Symbol	Value	Unit
Peak Pulse Power (8/20μs)	Ppk	400	W
Peak Pulse Current (8/20μs)	I_{PP}	24	A
ESD per IEC 61000−4−2 (Air) ESD per IEC 61000−4−2 (Contact)	V_{ESD}	±15 ±8	kV
Operating Temperature Range	T_J	−55 to +125	°C
Storage Temperature Range	Tstg	−55 to +150	°C

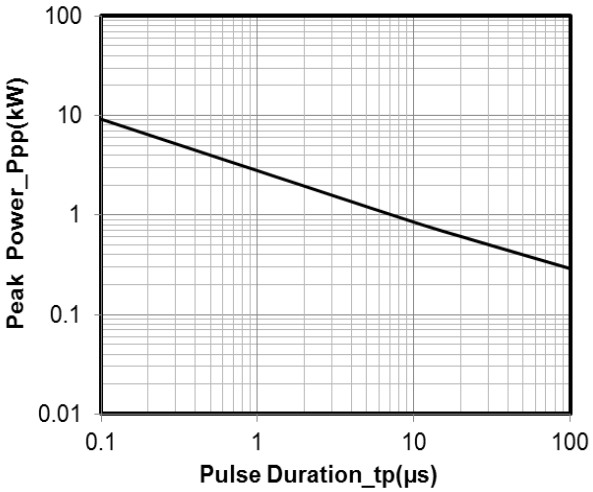
Electrical Characteristics (T_A=25°C unless otherwise specified)

Parameter	Symbol	Min	Typ	Max	Unit	Test Condition
Reverse Working Voltage	V_{RWM}			2.8	V	
Breakdown Voltage	V_{BR}	3.0			V	I_T = 2μA
	V_{SB}	2.8			V	I_{SB}= 50mA
Reverse Leakage Current	I_R		0.001	1	μA	V_{RWM} = 2.8V
Clamping Voltage	V_C		6		V	I_{PP} = 1A (8 x 20μs pulse)
Clamping Voltage	V_C		10		V	I_{PP} = 10A (8 x 20μs pulse)
Clamping Voltage	V_C		16	20	V	I_{PP} = 24A (8 x 20μs pulse)
Junction Capacitance	C_J		1	2	pF	VR = 0V, f = 1MHz

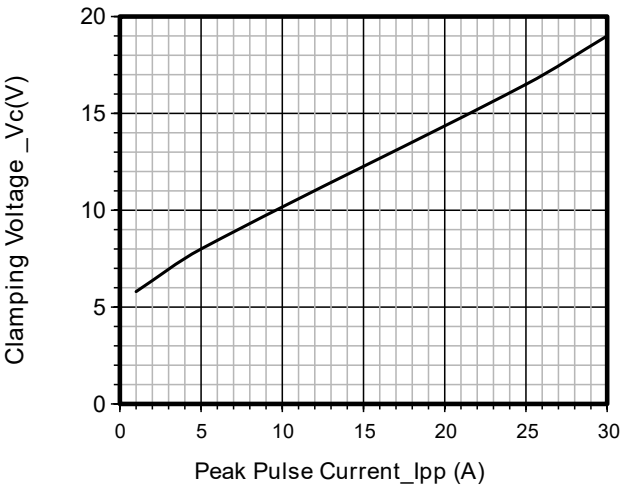
Typical Performance Characteristics (T_A=25°C unless otherwise Specified)



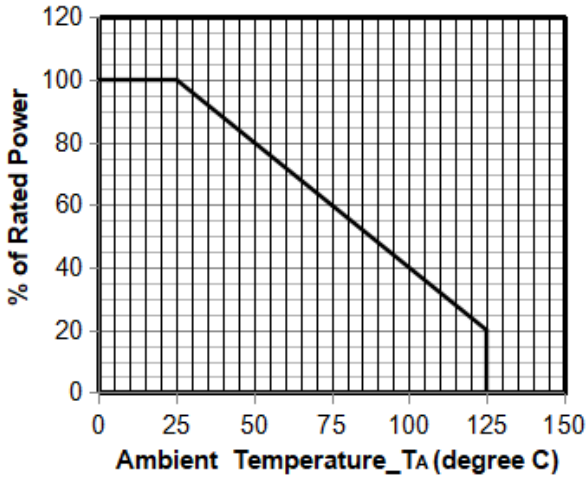
Junction Capacitance vs. Reverse Voltage



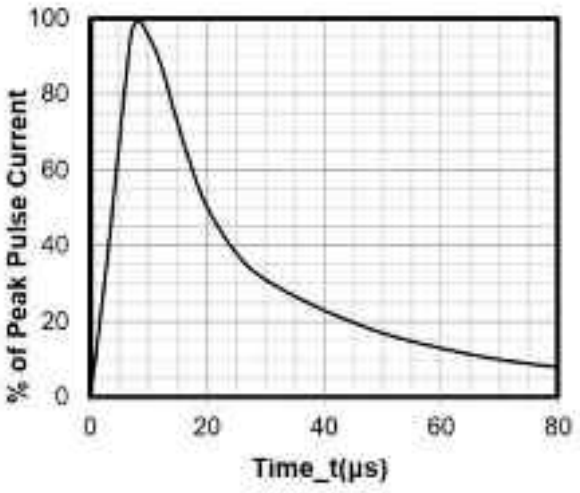
Peak Pulse Power vs. Pulse Time



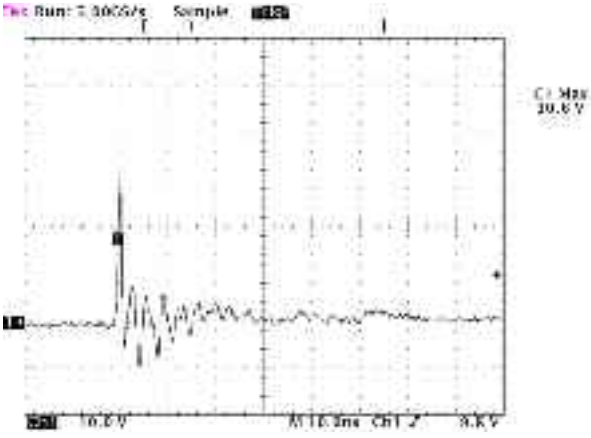
Clamping Voltage vs. Peak Pulse Current



Power Derating Curve



8 X 20μs Pulse Waveform

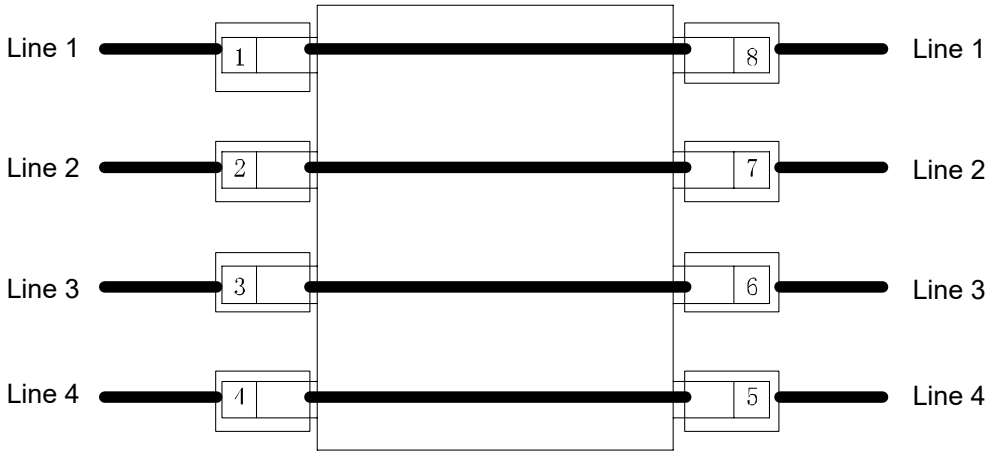


Note：Data is taken with a 10x attenuator

ESD Clamping Voltage
8 kV Contact per IEC61000−4−2

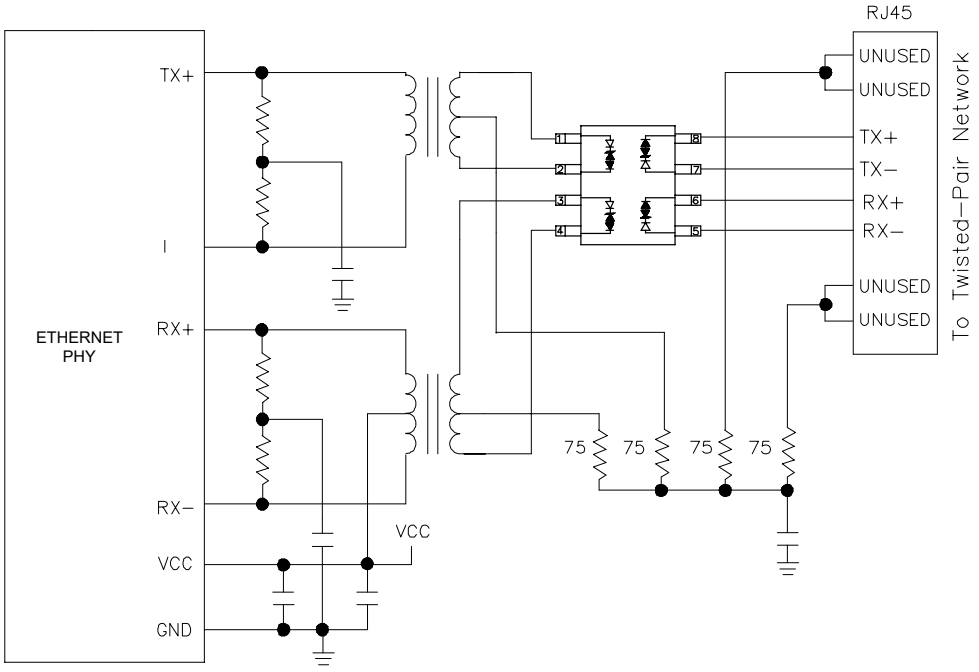
Typical Application

The SLVU2.8-4 is designed such that the data lines are routed through the device. The first line pair enters at pins 1 and 2 and exit at pins 8 and 7 respectively. The second line pair enters at pins 3 and 4 and exits at pins 6 and 5. The traces must be connected at the bottom of the device as shown.

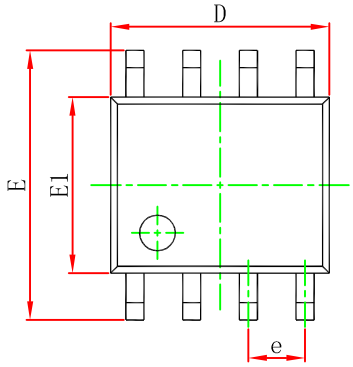


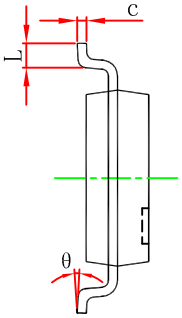
Low capacitance protection of two differential line pairs

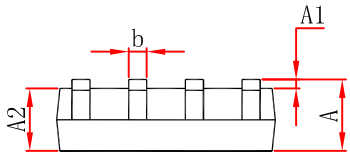
SLVU2.8-4 on Ethernet Application



SOP-8 Package Outline Drawing

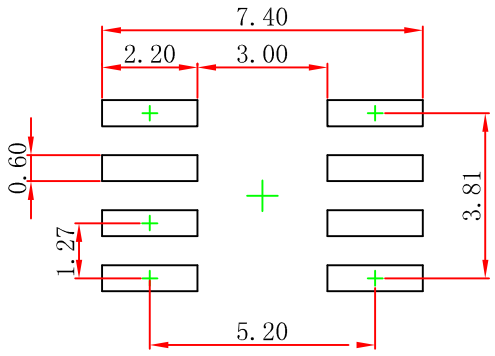






Symbol	Dimensions In Millimeters		Dimensions In Inches	
	Min	**Max**	**Min**	**Max**
A	1.350	1.750	0.053	0.069
A1	0.100	0.250	0.004	0.010
A2	1.350	1.550	0.053	0.061
b	0.330	0.510	0.013	0.020
c	0.170	0.250	0.007	0.010
D	4.800	5.000	0.189	0.197
e	1.270（BSC）		0.050（BSC）	
E	5.800	6.200	0.228	0.244
E1	3.800	4.000	0.150	0.157
L	0.400	1.270	0.016	0.050
θ	0°	8°	0°	8°

SOP8 Suggested Pad Layout



Note:
1.Controlling dimension:in millimeters.
2.General tolerance:± 0.05mm.
3.The pad layout is for reference purposes only.